# 2SC5788

# Silicon NPN epitaxial planar type

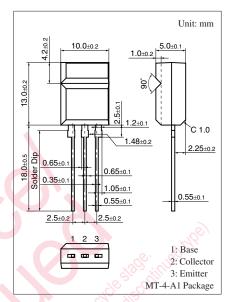
Power supply for Audio & Visual equipments such as TVs and VCRs Industrial equipments such as DC-DC converters

#### ■ Features

- ullet High-speed switching ( $t_{stg}$ : storage time/ $t_f$ : fall time is short)
- ullet Low collector to emitter saturation voltage  $V_{CE(sat)}$
- Superior forward current transfer ratio h<sub>FE</sub> linearity
- Allowing automatic insertion with radial taping

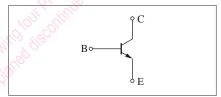
## ■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (En	V <sub>CBO</sub>	60	V	
Collector-emitter voltage	V <sub>CEO</sub>	60	V	
Emitter-base voltage (Collector open)		$V_{EBO}$	6	V
Collector current		I <sub>C</sub>	3	A
Peak collector current		I <sub>CP</sub>	6	A
Collector power	$T_C = 25^{\circ}C$	$P_{C}$	15	W
dissipation	$T_a = 25^{\circ}C$		2	
Junction temperature		$T_{j}$	150	°C
Storage temperature		$T_{stg}$	<b>−55</b> ~ <b>+150</b>	°C



Marking Symbol: C5788

#### Internal Connection



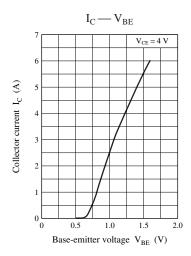
### ■ Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

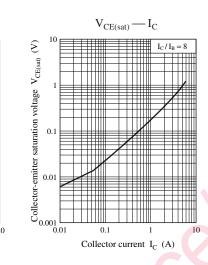
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_C = 10 \text{ mA}, I_B = 0$	60			V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = 60 \text{ V}, I_E = 0$			100	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = 60 \text{ V}, I_{B} = 0$			100	μΑ
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = 6 \text{ V}, I_C = 0$			1	mA
Forward current transfer ratio	${ m h_{FE1}}^*$	$V_{CE} = 4 \text{ V}, I_{C} = 1 \text{ A}$	120		320	_
	h <sub>FE2</sub>	$V_{CE} = 4 \text{ V}, I_{C} = 3 \text{ A}$	40			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = 3 \text{ A}, I_B = 375 \text{ mA}$			0.8	V
Transition frequency	$f_T$	$V_{CE} = 10 \text{ V}, I_{C} = 0.1 \text{ A}, f = 10 \text{ MHz}$		180		MHz
Turn-on time	t <sub>on</sub>	I <sub>C</sub> = 1 A, Resistance loaded		0.2	0.3	μs
Storage time	t <sub>stg</sub>	$I_{B1} = 0.1 \text{ A}, I_{B2} = -0.1 \text{ A}$		0.55	0.7	μs
Fall time	$t_{\rm f}$	$V_{CC} = 50 \text{ V}$		0.1	0.15	μs

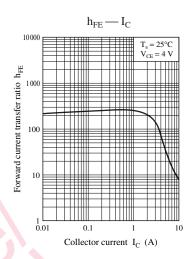
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

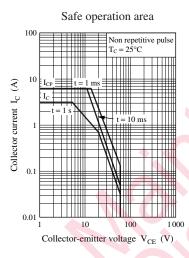
### 2. \*: Rank classification

Rank	Р	Q
h <sub>FE1</sub>	160 to 320	120 to 250









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